



US 20230230877A1

(19) **United States**(12) **Patent Application Publication**
Chung et al.(10) **Pub. No.: US 2023/0230877 A1**(43) **Pub. Date: Jul. 20, 2023**(54) **INTEGRATED CIRCUIT INTERCONNECT
STRUCTURE HAVING DISCONTINUOUS
BARRIER LAYER AND AIR GAP****Publication Classification**

(51) **Int. Cl.**
H01L 21/768 (2006.01)
H01L 23/522 (2006.01)
H01L 23/532 (2006.01)

(52) **U.S. Cl.**
CPC *H01L 21/76834* (2013.01); *H01L 23/5226*
(2013.01); *H01L 23/5329* (2013.01); *H01L*
21/76877 (2013.01); *H01L 21/76832*
(2013.01); *H01L 21/7682* (2013.01); *H01L*
21/76819 (2013.01)

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(TW)(21) Appl. No.: **18/183,004**(22) Filed: **Mar. 13, 2023****Related U.S. Application Data**(63) Continuation of application No. 17/213,888, filed on
Mar. 26, 2021, now Pat. No. 11,605,558.(57) **ABSTRACT**

A semiconductor structure includes a first dielectric layer, a first metallic feature over the first dielectric layer, an air gap over the first dielectric layer and adjacent to the first metallic feature, a second dielectric layer disposed above the air gap and on a sidewall of the first metallic feature, and a third dielectric layer disposed above the air gap and on a sidewall of the second dielectric layer. A lower portion of the first metallic feature is exposed in the air gap. The third and the second dielectric layers are substantially co-planar.

